

isc N-Channel MOSFET Transistor

FDP2532

• FEATURES

- With TO-220 packaging
- High speed switching
- Low gate input resistance
- Standard level gate drive
- Easy to use
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• APPLICATIONS

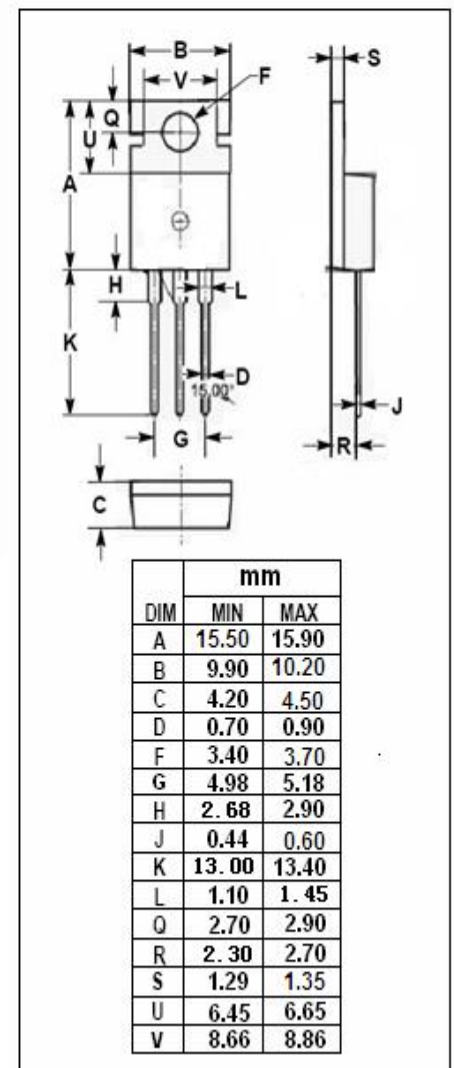
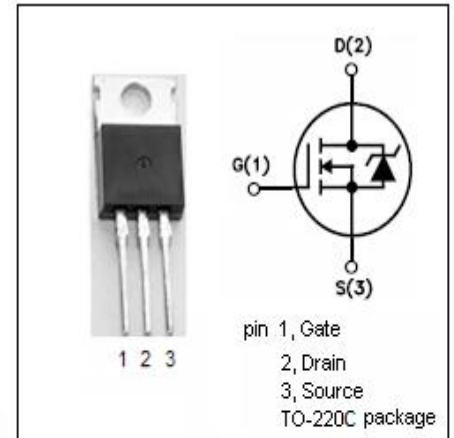
- Power supply
- Switching applications

• ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	150	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-Continuous; @ $T_c=25^{\circ}\text{C}$ $T_c=100^{\circ}\text{C}$	79 56	A
I_{DM}	Drain Current-Single Pulsed	300	A
P_D	Total Dissipation	310	W
T_j	Operating Junction Temperature	175	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~175	$^{\circ}\text{C}$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	0.48	$^{\circ}\text{C}/\text{W}$
$R_{th(ch-a)}$	Channel-to-ambient thermal resistance	62	$^{\circ}\text{C}/\text{W}$



isc N-Channel MOSFET Transistor**FDP2532****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V; I_D=0.25mA$	150			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=0.25mA$	2.0		4.0	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V; I_D=33A$		14	16	$m\Omega$
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V; V_{DS}=0V$			± 0.1	μA
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=120V; V_{GS}=0V; T_J=25^{\circ}\text{C}$ $V_{DS}=120V; V_{GS}=0V; T_J=150^{\circ}\text{C}$			1 250	μA
V_{SDF}	Diode forward voltage	$I_{SD}=1A, V_{GS}=0V$			1.0	V